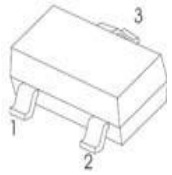
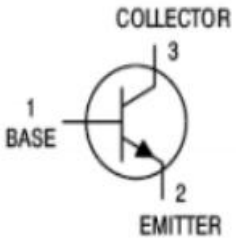
TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors

SOT-23





1.BASE
2.EMITTER
3.COLLECTOR

Features

※ High transition frequency
※ Small rbb'·Cc and high gain.
※ Small NF.

ABSOLUTE MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	VCBO	20	V
Collector-Emitter Voltage	VCEO	11	V
Emitter-Base Voltage	VEBO	3	V
Collector Current	IC	50	A
Collector Power Dissipation	PC	200	mW
Thermal Resistance From Junction To Ambient	RΘJA	200	℃/W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55～+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100μA, IE=0	20			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	11			V
Emitter-base breakdown voltage	V(BR)EBO	IE= 100μA, IC=0	3			V
Collector cut-off current	ICBO	VCB= 20 V , IE=0			0.5	μA
Emitter cut-off current	IEBO	VEB= 3V , IC=0			0.5	μA
DC current gain	hFE	VCE= 10V, IC= 5mA	82		250	
Collector-emitter saturation voltage	VCE(sat)	IC= 10 mA, IB= 5mA			0.5	V
Base-emitter saturation voltage	VBE(sat)	IC= 10 mA, IB= 5mA			1.2	V
Transition frequency	fT	VCE=10V, IC= 10mA f=500MHz,	1.4	3.2		GHz
Collector output capacitance	Cob	VCB = 10 V, IE = 0 mA, f = 1 MHz			1.5	PF
Collector-base time constant	rbb'.Cc	VCB = 10 V, IC = 10 mA, f=31.8 MHz,		4	12	ps
Noise figure	NF	VCE = 6 V, IC = 2 mA, f = 500MHz, Rg=50Ω		3.5		dB

CLASSIFICATION OF hFE

TYPE	2SC3356	2SC3356	2SC3356
Range	82-180	100-200	120-240
MARKING	R23	R24	R25

单击下面可查看定价，库存，交付和生命周期等信息

>>DIOS(迪恩思)